IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: **Kenji IMANISHI**

Serial No.: **Not Yet Assigned**

Filed: **October 19, 2001**

For: **A FIELD-EFFECT TRANSISTOR USING A GROUP III-V COMPOUND SEMICONDUCTOR**

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Date: October 19, 2001

Sir:

Prior to calculation of the filing fee and examination of this application, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 5 through 7 as follows:

5. (Amended) The high electron mobility transistor as described in claim 3, wherein the thickness of said first channel layer is 3~7 nm.

6. (Amended) The high electron mobility transistor as described in claim 3, wherein the thickness of said second channel layer is 10~20 nm.

7. (Amended) The high electron mobility transistor as described in claim 3, wherein the composition ratio (1-z) of Al element in said second channel layer is 0.05~0.5.

REMARKS

The above amendment to the claims has been made to correct the multiple dependency of the claims and to place the application in better condition for examination.

Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The attached page is captioned "Version with Markings to Show Changes Made."

In the event that any fees are due in connection with this paper, please charge our Deposit Account No. 01-2340.

Respectfully submitted,

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Claims 5 through 7 have been amended as follows:

5. The high electron mobility transistor as described in claim 3 ~~or claim 4~~, wherein the thickness of said first channel layer is 3~7 nm..

6. The high electron mobility transistor as described in claim 3 ~~or claim 4~~, wherein the thickness of said second channel layer is 10~20 nm.

7. The high electron mobility transistor as described in claim 3 ~~or claim 4~~, wherein the composition ratio (1-z) of Al element in said second channel layer is 0.05~0.5.